

PZTA92T1G, NSVPZTA92T1G

High Voltage Transistor

PNP Silicon

Features

- Complement to PZTA42T1G
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-300	Vdc
Collector-Base Voltage	V_{CBO}	-300	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current	I_C	-500	mAdc
Total Power Dissipation up to @ $T_A = 25^\circ\text{C}$ (Note 1)	P_D	1.5	W
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a FR-4 glass epoxy printed circuit board
1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83.3	$^\circ\text{C/W}$

2. Device mounted on a FR-4 glass epoxy printed circuit board
1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.

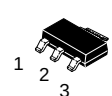
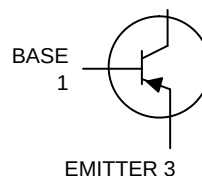


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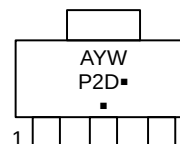
SOT-223 PACKAGE PNP SILICON HIGH VOLTAGE TRANSISTOR SURFACE MOUNT

COLLECTOR 2,4



SOT-223
CASE 318E
STYLE 1

MARKING DIAGRAM



P2D = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
PZTA92T1G, NSVPZTA92T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSVPZTA92T3G	SOT-223 (Pb-Free)	4,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

PZTA92T1G, NSVPZTA92T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (Note 3) (I _C = -1.0 mA, I _B = 0)	V _{(BR)CEO}	-300	-	Vdc
Collector-Base Breakdown Voltage (I _C = -100 μA, I _E = 0)	V _{(BR)CBO}	-300	-	Vdc
Emitter-Base Breakdown Voltage (I _E = -100 μA, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector-Base Cutoff Current (V _{CB} = -200 Vdc, I _E = 0)	I _{CBO}	-	-0.25	μA
Emitter-Base Cutoff Current (V _{BE} = -3.0 Vdc, I _C = 0)	I _{EBO}	-	-0.1	μA
ON CHARACTERISTICS				
DC Current Gain (I _C = -1.0 mA, V _{CE} = -10 Vdc) (I _C = -10 mA, V _{CE} = -10 Vdc) (I _C = -30 mA, V _{CE} = -10 Vdc)	h _{FE}	25 40 40	- - -	-
Saturation Voltages (I _C = -20 mA, I _B = -2.0 mA) (I _C = -20 mA, I _B = -2.0 mA)	V _{CE(sat)} V _{BE(sat)}	- -	-0.5 -0.9	Vdc
DYNAMIC CHARACTERISTICS				
Collector-Base Capacitance @ f = 1.0 MHz (V _{CB} = -20 Vdc, I _E = 0)	C _{cb}	-	6.0	pF
Current-Gain - Bandwidth Product (I _C = -10 mA, V _{CE} = -20 Vdc, f = 100 MHz)	f _T	50	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test Conditions, t_p = 300 μs, δ 0.02.

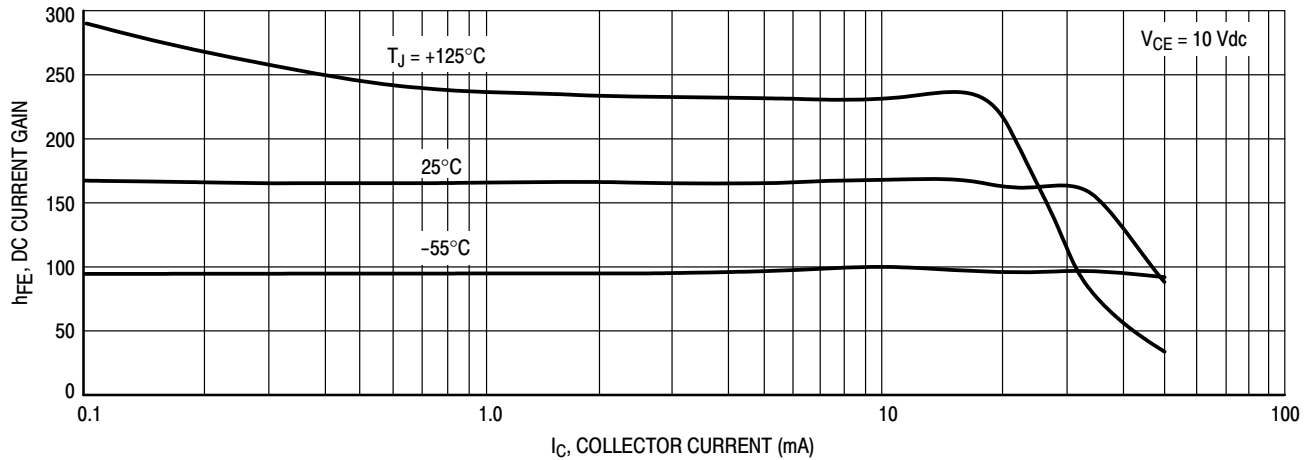


Figure 1. DC Current Gain

PZTA92T1G, NSVPZTA92T1G

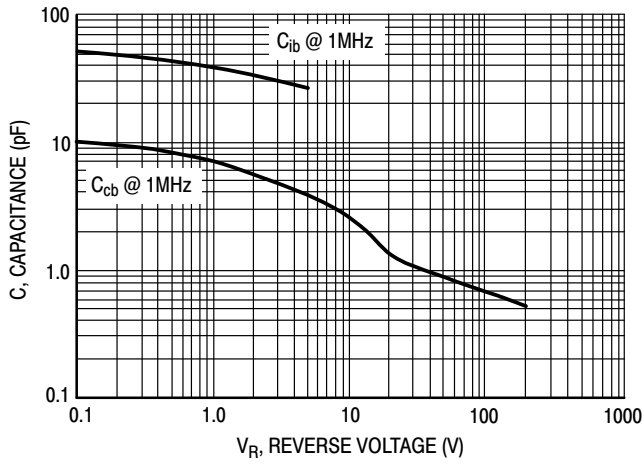


Figure 2. Capacitance

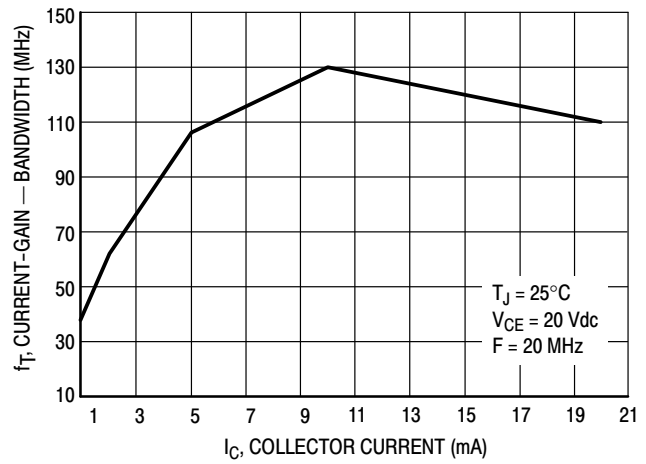


Figure 3. Current-Gain - Bandwidth

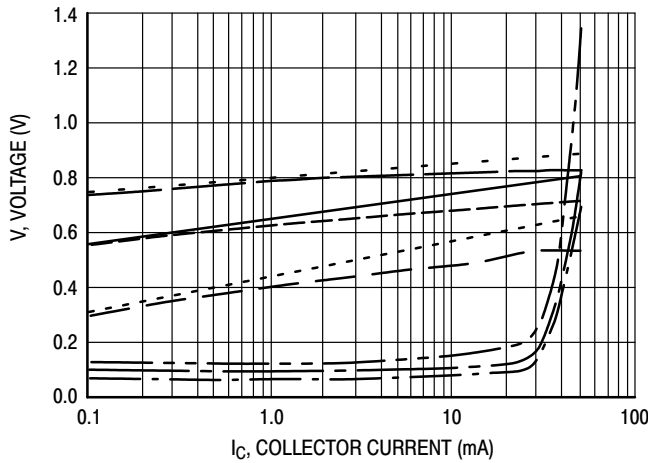


Figure 4. "ON" Voltages

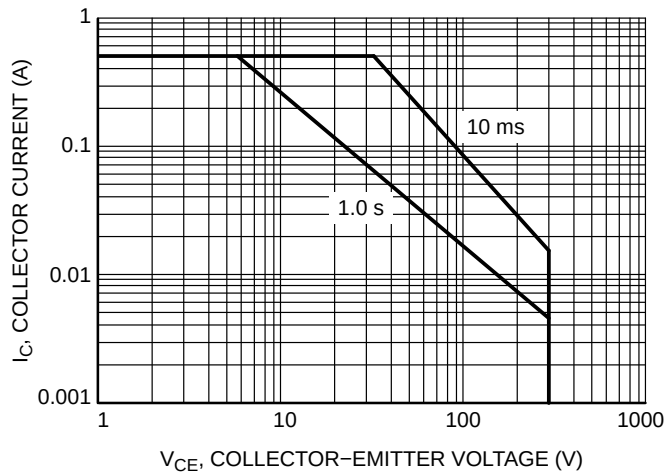
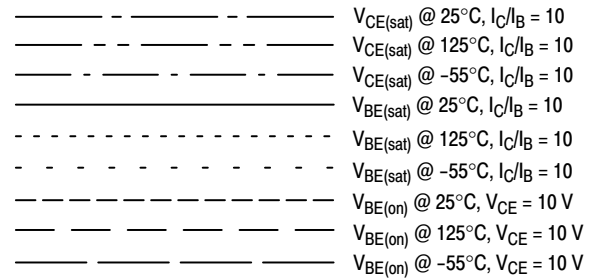


Figure 5. Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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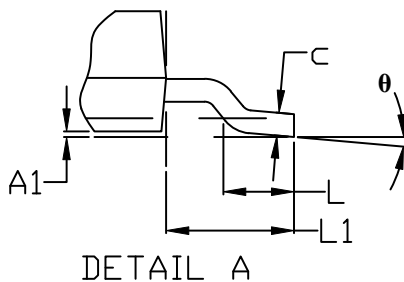
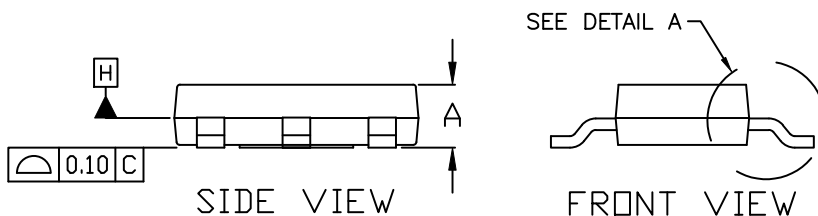
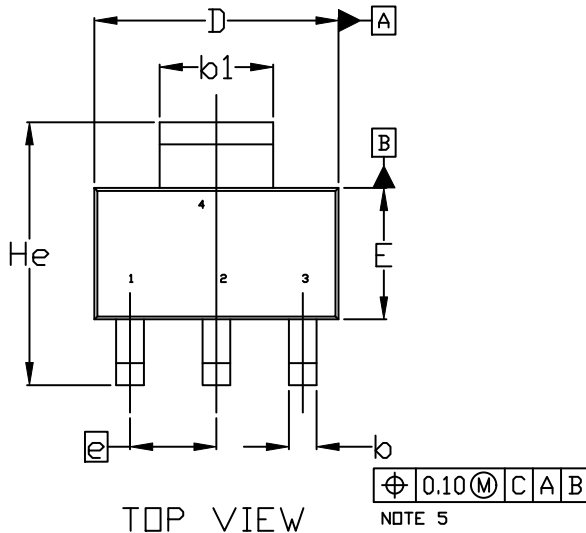
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SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

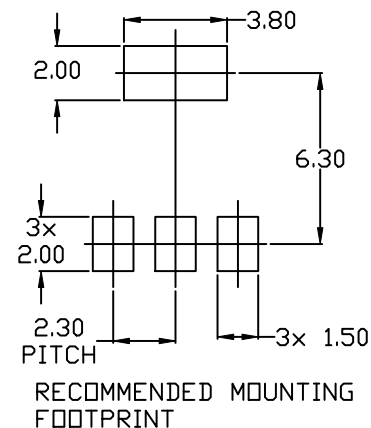
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NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



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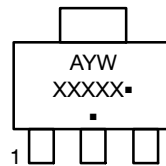
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SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

**GENERIC
MARKING DIAGRAM***



A = Assembly Location
 Y = Year
 W = Work Week
 XXXXX = Specific Device Code
 ■ = Pb-Free Package

(Note: Microdot may be in either location)
 *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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